



US 20240213327A1

(19) **United States**

(12) **Patent Application Publication**
KIM et al.

(10) **Pub. No.: US 2024/0213327 A1**

(43) **Pub. Date: Jun. 27, 2024**

(54) **SUPERLATTICE BUFFER STRUCTURE AND SEMICONDUCTOR DEVICE HAVING THE SAME**

Publication Classification

(51) **Int. Cl.**

H01L 29/15 (2006.01)

H01L 29/20 (2006.01)

H01L 29/778 (2006.01)

(52) **U.S. Cl.**

CPC **H01L 29/155** (2013.01); **H01L 29/2003** (2013.01); **H01L 29/7786** (2013.01)

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(21) Appl. No.: **18/485,740**

(22) Filed: **Oct. 12, 2023**

(30) **Foreign Application Priority Data**

Dec. 27, 2022 (KR) 10-2022-0186375

(57)

ABSTRACT

Provided are a superlattice buffer structure and a semiconductor device having the superlattice buffer structure. The superlattice buffer structure includes a plurality of superlattice blocks, and each of the plurality of superlattice blocks has a structure in which a first layer including $\text{Al}(1-x)\text{Ga}x\text{N}$ ($0 \leq x \leq 1$) and a second layer including $\text{Al}(1-y)\text{Ga}y\text{N}$ ($0 \leq y \leq 1$, $x > y$) are alternately stacked on each other.

